P-Channel 60-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

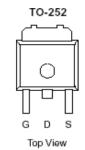
Typical Applications:

- AEC-Q101 qualified and PPAP capable
- DC/DC Conversion Circuits
- Motor Drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
-60	90 @ V _{GS} = -10V	-20	
	$108 @ V_{GS} = -4.5V$	-18	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			-60	V		
Gate-Source Voltage			±20			
Continuous Drain Current a	T _C =25°C	I _D	-20 A			
Pulsed Drain Current ^b			-80	A		
Continuous Source Current (Diode Conduction) ^a			-20	Α		
Power Dissipation ^a	T _C =25°C	P_D	50	W		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

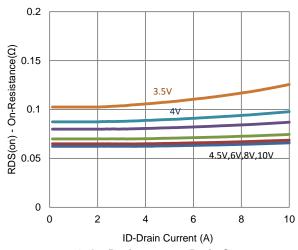
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtara Brain Current	lana	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-30			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$			90	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_{D} = -9 \text{ A}$			108	11122	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -10 \text{ A}$		13		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -10 \text{ A}, V_{GS} = 0 \text{ V}$		1		V	
	Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		10		nC	
Gate-Source Charge	Q_gs	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -2 \text{ A}$		5.0			
Gate-Drain Charge	Q_gd	1 ₀ – 271		3.3			
Turn-On Delay Time	$t_{d(on)}$	V 20 V B = 15 O		6			
Rise Time	t _r	$V_{DS} = -30 \text{ V}, R_L = 15 \Omega,$ $I_D = -2 \text{ A},$		5		ns	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		38			
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		14			
Input Capacitance	C _{iss}			1142			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$	_	84		pF	
Reverse Transfer Capacitance	C _{rss}]		59	_		

Notes

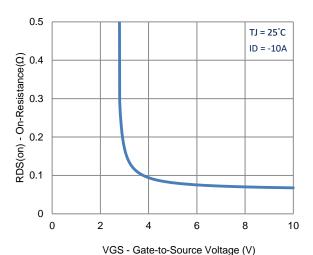
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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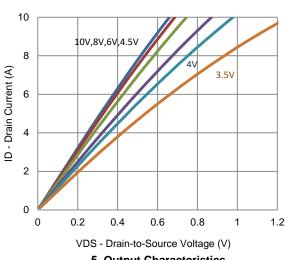
Typical Electrical Characteristics



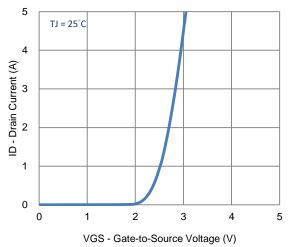
1. On-Resistance vs. Drain Current



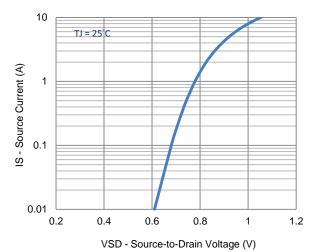
3. On-Resistance vs. Gate-to-Source Voltage



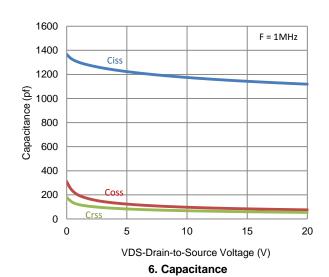
5. Output Characteristics



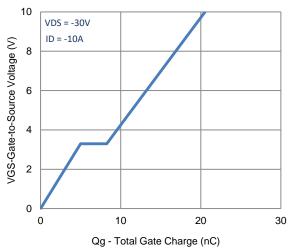
2. Transfer Characteristics



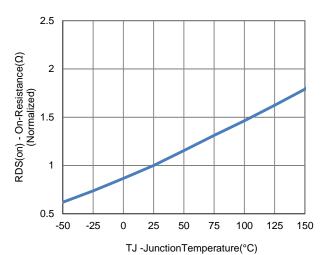
4. Drain-to-Source Forward Voltage



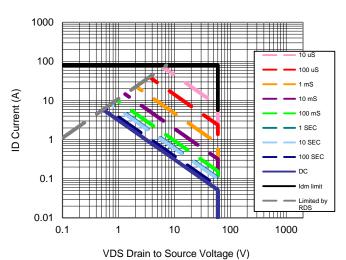
Typical Electrical Characteristics



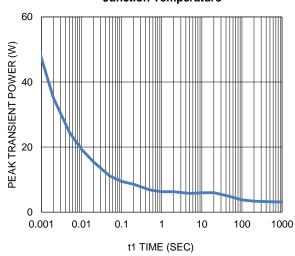
7. Gate Charge



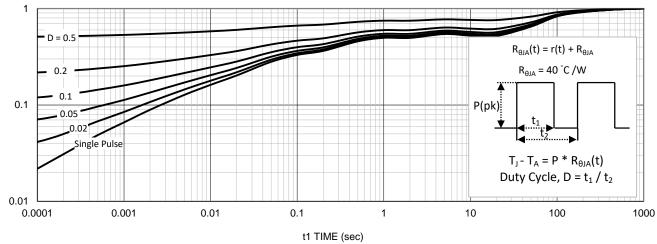
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

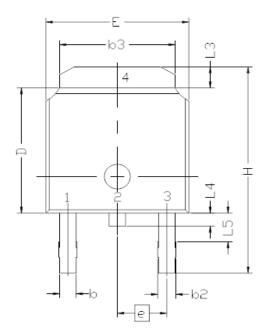


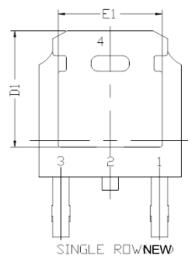
10. Single Pulse Maximum Power Dissipation

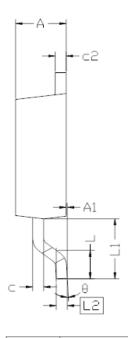


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVADDI	DIMENS:	[DNAL	REQMTS		
SYMBOL	MIN	NDM	MAX		
E	6.40	6.60	6.731		
L	1.40	1.52	1.77		
_L1	2.743 RÉF				
_L2		508 BS			
L3	0,89		1.27		
L4	0.64		1.01		
L5					
D	6.00	6.10	6.223		
Н	9.40	10.00	10.40		
b	0.64	0.76	0,88		
b2	0.77	0.84	1.14		
b3	5,21	5.34	5.46		
е		286 BS			
Α	2,20	2,30	2.38		
A1	0		0.127		
_	0.45	0.50	0.60		
c2	0.45	0,50	0.58		
D1	5.30				
E1	4.40				
θ	0*		10°		

Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.